

FIRST PRELIMINARY AMENDMENT

October 20, 2000

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

In the Drawings:

Please transfer FIGS. 1 – 2, 3B – 3D, and 4 – 13 from the file of the issued '070 patent to the reissue file.

Please amend FIGS. 3A and 3E as requested in the enclosed Request for Drawing Change.

In the Specification:

In Column 3, line 6, please replace "PG1 and PG2" with [PG1 and PG2] TG1

G1 and TG2

In Column 4, please replace with "RATIO $\leq \frac{Tox_{ig}}{Tox_{pd}} \frac{W_{pd}/L_{pd}}{W_{ig}/L_{ig}} \frac{Vcc - Vt_{ig}}{Vcc - Vt_{pd}}$ " with

G2
[RATIO $\leq \frac{Tox_{ig}}{Tox_{pd}} \frac{W_{pd}/L_{pd}}{W_{ig}/L_{ig}} \frac{Vcc - Vt_{ig}}{Vcc - Vt_{pd}}$]

RATIO $\leq \frac{Tox_{ig}}{Tox_{pd}} \times \frac{W_{pd}/L_{pd}}{W_{ig}/L_{ig}} \times \frac{Vcc - Vt_{pd}}{Vcc - Vt_{ig}}$

In the Claims:

Please amend the claims as follows:

1. An SRAM memory cell comprising:

[a] first and second transfer gate transistors, the first transfer gate transistor having a first source/drain connected to a bit line and the second transfer gate transistor having a first source/drain connected to a complement bit line and each transfer gate transistor having a gate connected to a word line; [and]
G3
first and second pull-down transistors configured as a storage latch, the first pull-down transistor having a first source/drain connected to a second source/ drain of said